8-Channel Data Selector

The MC14512B is an 8-channel data selector constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. This data selector finds primary application in signal multiplexing functions. It may also be used for data routing, digital signal switching, signal gating, and number sequence generation.

Features

- Diode Protection on All Inputs
- Single Supply Operation
- 3-State Output (Logic "1", Logic "0", High Impedance)
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low–power TTL Loads or One Low–power Schottky TTL Load Over the Rated Temperature Range
- Pb–Free Packages are Available*

MAXIMUM RATINGS (Voltages Referenced to VSS)

Parameter	Symbol	Value	Unit
DC Supply Voltage Range	V _{DD}	-0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	V _{in} , V _{out}	–0.5 to V _{DD} + 0.5	V
Input or Output Current (DC or Transient) per Pin	I _{in} , I _{out}	±10	mA
Power Dissipation, Per Package (Note 1)	PD	500	mW
Ambient Temperature Range	T _A	-55 to +125	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Lead Temperature (8–Second Soldering)	ΤL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Temperature Derating: Plastic "P and D/DW"

Packages: - 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$

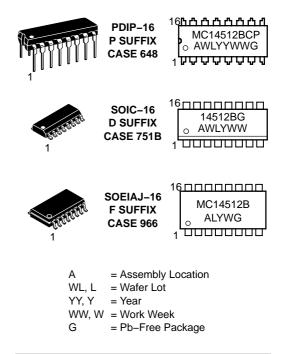
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

TRUTH TABLE

С	В	Α	Inhibit	Disable	Z
0	0	0	0	0	X0
0	0	1	0	0	X1
0	1	0	0	0	X2
0	1	1	0	0	Х3
1	0	0	0	0	X4
1	0	1	0	0	X5
1	1	0	0	0	X6
1	1	1	0	0	Х7
Х	Х	Х	1	0	0
Х	Х	Х	Х	1	High Impedance

NOTE: X = Don't Care

ORDERING INFORMATION

Device	Package	Shipping [†]
MC14512BCP	PDIP-16	
MC14512BCPG	PDIP-16 (Pb-Free)	25 Units / Rail
MC14512BD	SOIC-16	
MC14512BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14512BDR2	SOIC-16	
MC14512BDR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC14512BF	SOEIAJ-16	
MC14512BFG	SOEIAJ-16 (Pb-Free)	50 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PIN ASSIGNMENT							
X0 [1•	16					
Х1 [15	DIS				
X2 [3	14	Πz				
ХЗ 🛛	4	13	l C				

X4 [] 5 X5 [] 6

X6 [] 7 V_{SS} [] 8 12 🛛 B

11 🛛 A 10 🗍 INH

9 🛛 X7

MC14512B

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				- 5	5°C		25°C	_	125	S°C	
Characteristic		Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
$V_{in} = 0 \text{ or } V_{DD}$	"1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95		Vdc
$ Input Voltage \\ (V_O = 4.5 \text{ or } 0.5 \text{ Vdc}) \\ (V_O = 9.0 \text{ or } 1.0 \text{ Vdc}) \\ (V_O = 13.5 \text{ or } 1.5 \text{ Vdc}) $	"0" Level	V _{IL}	5.0 10 15	_ _ _	1.5 3.0 4.0	_ _ _	2.25 4.50 6.75	1.5 3.0 4.0	_ _ _	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V _{IH}	5.0 10 15	3.5 7.0 11		3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11		Vdc
$\begin{array}{l} \text{Output Drive Current} \\ (\text{V}_{\text{OH}} = 2.5 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 4.6 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 9.5 \ \text{Vdc}) \\ (\text{V}_{\text{OH}} = 13.5 \ \text{Vdc}) \end{array}$	Source	I _{ОН}	5.0 5.0 10 15	- 3.0 - 0.64 - 1.6 - 4.2	- - -	- 2.4 - 0.51 - 1.3 - 3.4	- 4.2 - 0.88 - 2.25 - 8.8	- - -	- 1.7 - 0.36 - 0.9 - 2.4		mAc c
$\begin{array}{l} ({\sf V}_{\sf OL}=0.4 \; {\sf Vdc}) \\ ({\sf V}_{\sf OL}=0.5 \; {\sf Vdc}) \\ ({\sf V}_{\sf OL}=1.5 \; {\sf Vdc}) \end{array}$	Sink	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4		mAc c
Input Current		l _{in}	15	-	± 0.1	_	±0.00001	± 0.1	-	± 1.0	μAd
Input Capacitance (V _{in} = 0)		C _{in}	-	-	_	_	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I _{DD}	5.0 10 15	_ _ _	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μAdo
Total Supply Current (Note (Dynamic plus Quiescer Per Package) (C _L = 50 pF on all outpu buffers switching)	nt,	Ι _Τ	5.0 10 15			$I_{T} = (1$.8 μΑ/kHz) f .6 μΑ/kHz) f .4 μΑ/kHz) f	$+ I_{DD}$			μAde
3–State Leakage Current		I _{TL}	15	-	± 0.1	-	± 0.0001	± 0.1	-	± 3.0	μAdo

Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25°C.

4. To calculate total supply current at loads other than 50 pF: $I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50)$ Vfk where: I_T is in μ A (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.001.

SWITCHING CHARACTERISTICS (Note 5) (C_L = 50 pF, T_A = 25°C, See Figure 1)

			All Types		
Characteristic	Symbol	V _{DD}	Typ (Note 6)	Max	Unit
Output Rise and Fall Time t_{TLH} , $t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$ t_{TLH} , $t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$ t_{TLH} , $t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$	t _{TLH} , t _{THL}	5.0 10 15	100 50 40	200 100 80	ns
Propagation Delay Time (Figure 2) Inhibit, Control, or Data to Z	t _{PLH}	5.0 10 15	330 125 85	650 250 170	ns
Propagation Delay Time (Figure 2) Inhibit, Control, or Data to Z	t _{PHL}	5.0 10 15	330 125 85	650 250 170	ns
3–State Output Delay Times (Figure 3) "1" or "0" to High Z, and High Z to "1" or "0"	t _{PHZ} , t _{PLZ} , t _{PZH} , t _{PZL}	5.0 10 15	60 35 30	150 100 75	ns

The formulas given are for the typical characteristics only at 25°C.
 Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

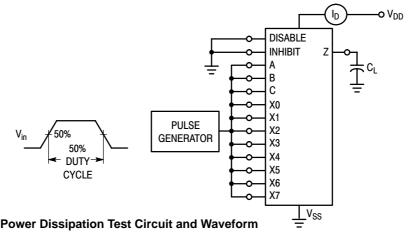


Figure 1. Power Dissipation Test Circuit and Waveform

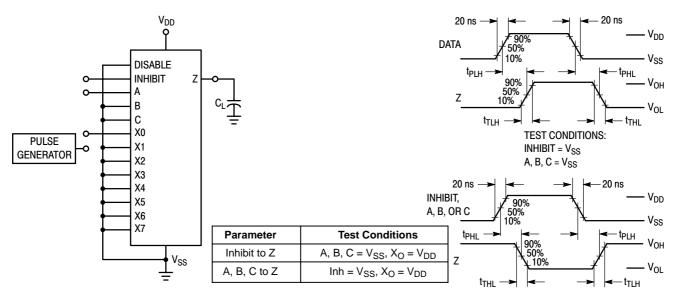


Figure 2. AC Test Circuit and Waveforms

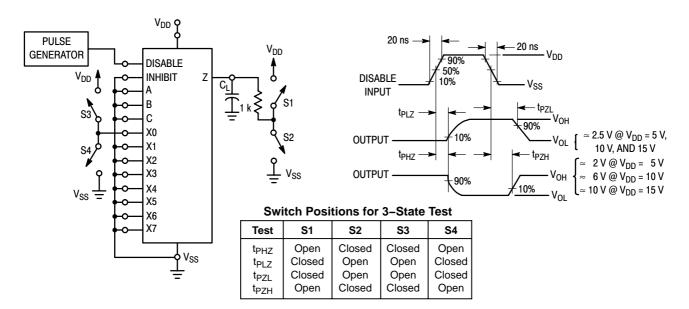
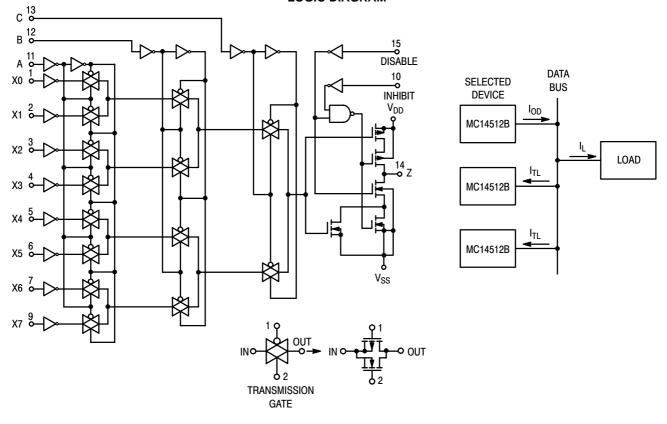


Figure 3. 3–State AC Test Circuit and Waveform

MC14512B





3-STATE MODE OF OPERATION

Output terminals of several MC14512B 8–Bit Data Selectors can be connected to a single date bus as shown. One MC14512B is selected by the 3–state control, and the remaining devices are disabled into a high–impedance "off" state. The number of 8–bit data selectors, N, that may be connected to a bus line is determined from the output drive current, I_{OD} , 3–state or disable output leakage current, I_{TL} , and the load current, I_L , required to drive the bus line

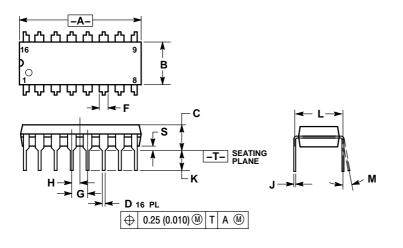
(including fanout to other device inputs), and can be calculated by:

$$N = \frac{I_{OD} - I_L}{I_{TL}} + 1$$

N must be calculated for both high and low logic state of the bus line.

PACKAGE DIMENSIONS

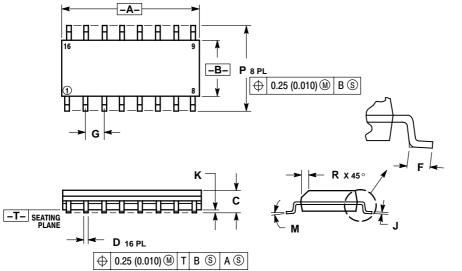
PDIP-16 CASE 648-08 ISSUE T



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL. 4. DIMENSION B DOES NOT INCLUDE MOLD ELASH
- MOLD FLASH. 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	BSC	2.54	BSC
Н	0.050	BSC	1.27	BSC
J	0.008	0.015	0.21	0.38
κ	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
М	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

SOIC-16 CASE 751B-05 **ISSUE J**



NOTES:

- NO LES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

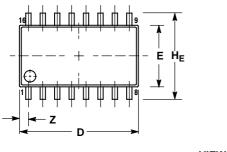
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)

- MAXIMUM MOLD PHOTHOSION 0. 19 (0.000) PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

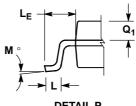
PACKAGE DIMENSIONS

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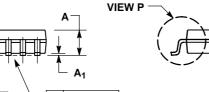


е

⊕ 0.13 (0.005) M







0.10 (0.004)

 \frown

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE
- MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.006) PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR BEFERENCE ONLY

 TELIMINET IONIZELIO ANLE ONOWITION REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

			-	
	MILLIN	IETERS	INC	HES
DIM	MIN	MIN MAX		MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
Г	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
Μ	0 °	10 °	0 °	10 °
Q1	0.70	0.90	0.028	0.035
Z		0.78		0.031

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